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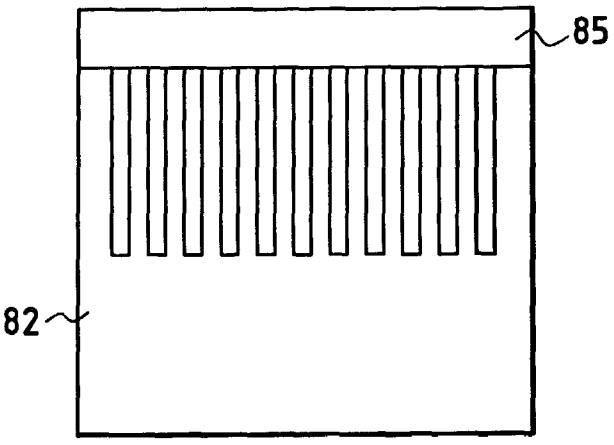
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(54) Title: SUBSTRATE ASSEMBLY FOR STRESSED SYSTEMS



(57) Abstract: The invention concerns a structure assembled from a film and a substrate (85, 82) respectively having a first thermal expansion coefficient and a second thermal expansion coefficient which differs from the first, and respectively having first and second assembly faces, motifs being formed in the second substrate (82), said motifs being elastic or being flexible in a plane parallel to the first and second assembly faces.

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